

Description

The FDV305N uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 20V I_D = 2.3 A$ $R_{DS(ON)} < 60m\Omega@ V_{GS} = 4.5V$

Application

Battery protection Load switch Uninterruptible power supply

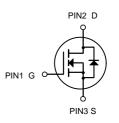
Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
FDV305N	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 $^\circ\!\!\!\mathrm{C}$ unless otherwise noted)

Parameter	Limit	Unit
Drain-Source Voltage	20	V
Gate-Source Voltage	±12	V
Drain Current-Continuous	2.3	A
Drain Current-Pulsed (Note 1)	16	A
Maximum Power Dissipation	0.9	W
Operating Junction and Storage Temperature Range	-55 To 150	°C
Thermal Resistance, Junction-to-Ambient (Note 2)	139	°C/W
	Drain-Source Voltage Gate-Source Voltage Drain Current-Continuous Drain Current-Pulsed (Note 1) Maximum Power Dissipation Operating Junction and Storage Temperature Range	Drain-Source Voltage20Gate-Source Voltage±12Drain Current-Continuous2.3Drain Current-Pulsed (Note 1)16Maximum Power Dissipation0.9Operating Junction and Storage Temperature Range-55 To 150





N-Channel MOSFET



Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V Ι _D =250μΑ	20	22	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =250µA	0.5	0.75	1.2	V
	Rds(on)	V _{GS} =2.5V, I _D =2.0A	-	54	72	mΩ
Drain-Source On-State Resistance		V _{GS} =4.5V, I _D =2.3A	-	48	60	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =2.3A	-	8	-	S
Input Capacitance	C _{lss}		-	260	-	PF
Output Capacitance	Coss	V _{DS} =10V,V _{GS} =0V,	-	48	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	27	-	PF
Turn-on Delay Time	td(on)		-	2.5	-	nS
Turn-on Rise Time	tr	V _{DD} =10V, R∟=3.3Ω	-	3.2	-	nS
Turn-Off Delay Time	td(off)	V_{GS} =4.5V,R _{GEN} =6 Ω	-	21	-	nS
Turn-Off Fall Time	t _f		-	3	-	nS
Total Gate Charge	Qg		-	2.9	5	nC
Gate-Source Charge	Q _{gs}	V _{DS} =10V,I _D =2.3A,	-	0.4	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	0.6	-	nC
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =2.3A	-	0.75	1.2	V
Diode Forward Current (Note 2)	ls		-	-	3.3	А

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

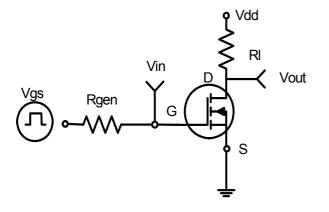


Figure 1:Switching Test Circuit

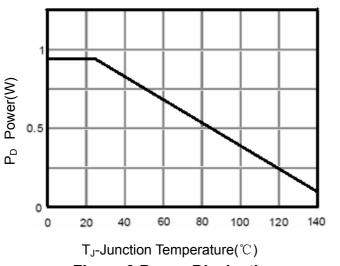
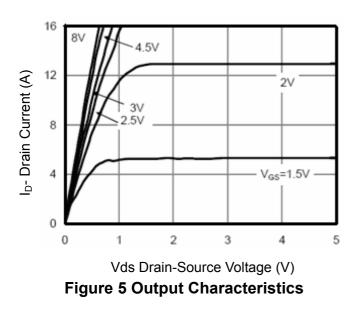
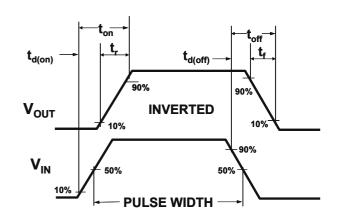


Figure 3 Power Dissipation







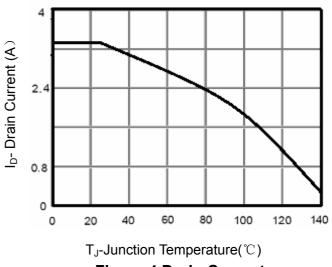


Figure 4 Drain Current

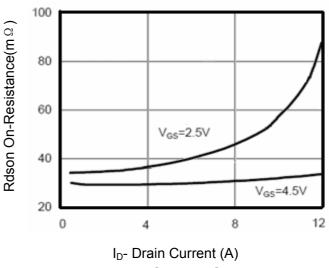
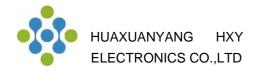
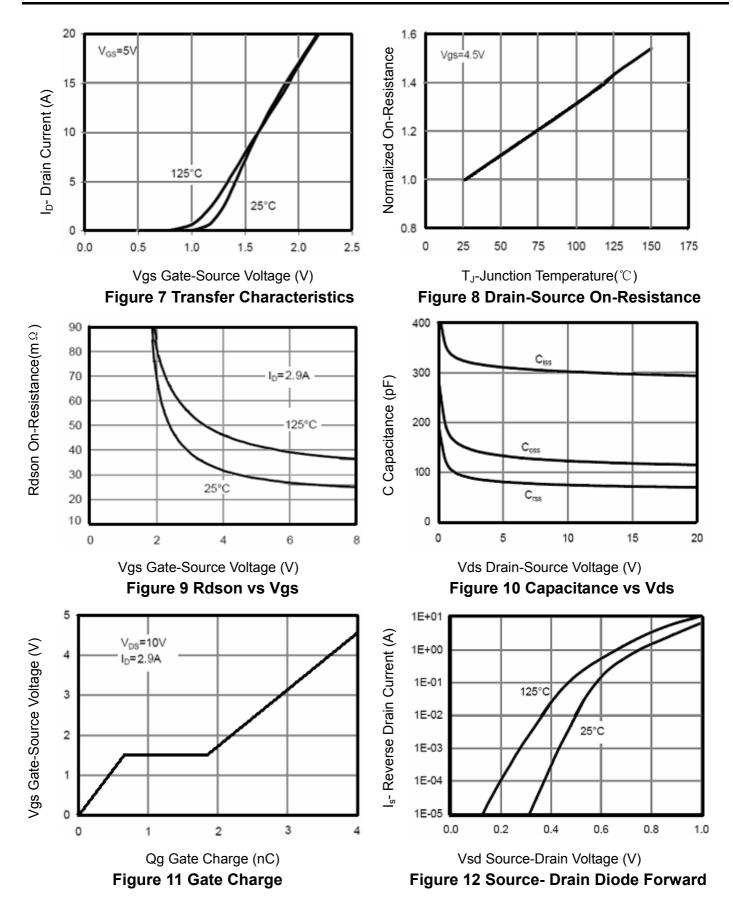


Figure 6 Drain-Source On-Resistance

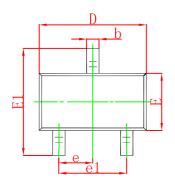


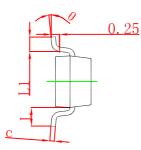
FDV305N N-Channel Enhancement Mode MOSFET

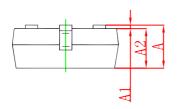




SOT-23 Package Outline Dimensions

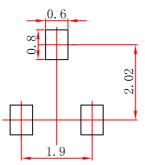






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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